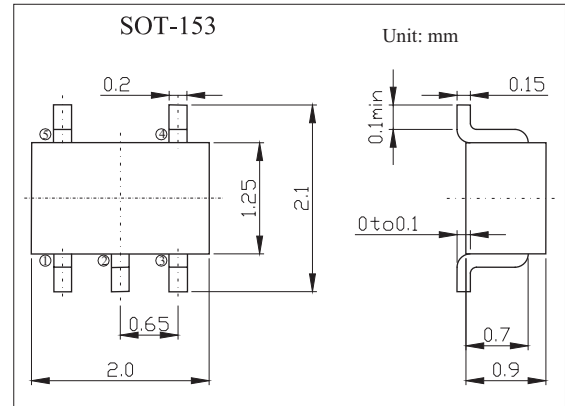
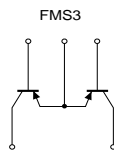


General purpose (Dual PNP Transistors)

FMS3

Features

High breakdown voltage

Power dissipation: $P_c=300\text{mW}$ Collector Current: $I_c=-50\text{mA}$ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-120	V
Collector-Emitter Voltage	V_{CE0}	-120	V
Emitter-Base Voltage	V_{EB0}	-5.0	V
Collector Current -Continuous	I_c	-50	mA
Collector Power Dissipation(TOTAL)	P_c	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CB0}$	$I_c = -50\mu\text{A}, I_E = 0$	-120			V
Collector-to-emitter breakdown voltage	$V_{(BR)CE0}$	$I_c = -1\text{mA}, I_B = 0$	-120			V
Emitter-to-base breakdown voltage	$V_{(BR)EB0}$	$I_E = -50\mu\text{A}, I_c = 0$	-5.0			V
Collector cutoff current	I_{cBO}	$V_{CB} = -100\text{V}, I_E = 0$			-0.5	μA
Collector cutoff current	I_{EBO}	$V_{CE} = -4.0\text{V}, I_c = 0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE} = -60\text{V}, I_c = -2.0\text{mA}$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10\text{mA}, I_B = -1.0\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE} = -12\text{V}, I_c = -2\text{mA}, f = 100\text{MHz}$		140		MHz

Marking

Marking	S3
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